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(71) Applicant: **FUJITSU LTD**
(72) Inventor: **NAKAI KENYA**
(74) Representative:

(54) MANUFACTURE OF SEMICONDUCTOR SUPERLATTICE

(57) Abstract:

PURPOSE: To form a Ge layer and an Si layer or a Ge-Si layer and an Si layer on an Si substrate, and also to put a hetero-epitaxial growth method, in which excellent crystal quality and high growth speed can be obtained, into practical use.

CONSTITUTION: The title semiconductor superlattice

manufacturing method is the method with which a Ge layer and an Si layer or Ge-Si layer and an Si layer are epitaxially grown on an Si substrate by conducting a depressed CVD method under the atmosphere containing oxidizing impurity gas of 1000ppb or lower using GeH₄ and trisilane (Si₃H₈) as raw gas and also using H₂ or inert gas as carrier gas.

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